METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

A technique includes: (a) storing a process gas in a storage fluidly connected to a space in which a substrate exists by a first section, (b) controlling a pressure in a second section, which is connected to a carrier gas supply source and the first section, to a predetermined pressure, (c) supplying the process gas to the substrate, the act of supplying the process gas including (c1) supplying the process gas stored in the storage to the substrate via the first section, and (d) supplying a carrier gas to the substrate via the first section and the second section, (d) being started after (b) and during (c), wherein a pressure inside the storage at a start timing of (d) is set to be equal to or higher than the predetermined pressure.

Figs. 4B and 4C